

P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|-----------------|-----------------------------|---------------------------|--------------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^{a, b} | Q_g (Typ.) |
| - 30 | 0.088 at $V_{GS} = - 10$ V | - 2.7 | 4.1 nC |
| | 0.138 at $V_{GS} = - 4.5$ V | - 2.2 | |

FEATURES

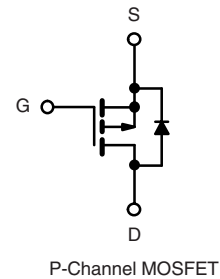
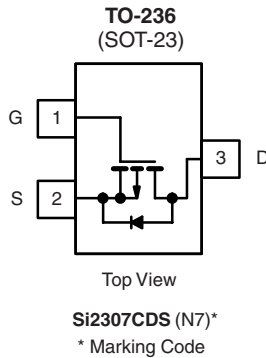
- Halogen-free Option Available
- TrenchFET[®] Power MOSFET



RoHS
COMPLIANT

APPLICATIONS

- Load Switch for Portable Devices



Ordering Information: Si2307CDS-T1-E3 (Lead (Pb)-free)
Si2307CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | | |
|--|----------------|------------------------|------|--|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V_{DS} | - 30 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current ($T_J = 150$ °C) ^{a, b} | $T_C = 25$ °C | - 3.5 | A | |
| | $T_C = 70$ °C | - 2.8 | | |
| | $T_A = 25$ °C | - 2.7 ^{a, b} | | |
| | $T_A = 70$ °C | - 2.2 ^{a, b} | | |
| Pulsed Drain Current (10 μ s Pulse Width) | I_{DM} | - 12 | A | |
| Continuous Source-Drain Diode Current ^{a, b} | $T_C = 25$ °C | - 1.5 | | |
| | $T_A = 25$ °C | - 0.91 ^{a, b} | | |
| Maximum Power Dissipation ^{a, b} | $T_C = 25$ °C | 1.8 | W | |
| | $T_C = 70$ °C | 1.14 | | |
| | $T_A = 25$ °C | 1.1 ^{a, b} | | |
| | $T_A = 70$ °C | 0.7 ^{a, b} | | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C | |
| Soldering Recommendations (Peak Temperature) ^c | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|------------|---------|---------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^{a, c} | R_{thJA} | 90 | 115 | °C/W | |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 55 | 70 | | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. $t = 5$ s.

c. Maximum under Steady State conditions is 166 °C/W.



| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|-------------------------|--|------|-------|-------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | - 30 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = -250\text{ }\mu\text{A}$ | | - 32 | | mV/°C |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | 4.5 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | - 1 | | - 3 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | - 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$ | | | - 1 | μA |
| | | $V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | - 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \leq 5\text{ V}, V_{GS} = -10\text{ V}$ | - 6 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}, I_D = -3.5\text{ A}$ | | 0.073 | 0.088 | Ω |
| | | $V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$ | | 0.110 | 0.138 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -10\text{ V}, I_D = -3.5\text{ A}$ | | 7 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 340 | | pF |
| Output Capacitance | C_{oss} | | | 67 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 51 | | |
| Total Gate Charge | Q_g | $V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$ | | 4.1 | 6.2 | nC |
| Gate-Source Charge | Q_{gs} | | | 1.3 | | |
| Gate-Drain Charge | Q_{gd} | | | 1.8 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | 10 | | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$ | | 40 | 60 | ns |
| Rise Time | t_r | | | 40 | 60 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 20 | 40 | |
| Fall Time | t_f | | | 17 | 30 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$ | | 5.5 | 10 | |
| Rise Time | t_r | | | 13 | 25 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 17 | 30 | |
| Fall Time | t_f | | | 7.7 | 15 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | | | - 1.5 | A |
| Pulse Diode Forward Current | I_{SM} | | | | - 12 | |
| Body Diode Voltage | V_{SD} | $I_S = -0.75\text{ A}, V_{GS} = 0\text{ V}$ | | - 0.8 | - 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = -2.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | | 17 | 30 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 11 | 20 | nC |
| Reverse Recovery Fall Time | t_a | | | 12 | | ns |
| Reverse Recovery Rise Time | t_b | | | 5 | | |

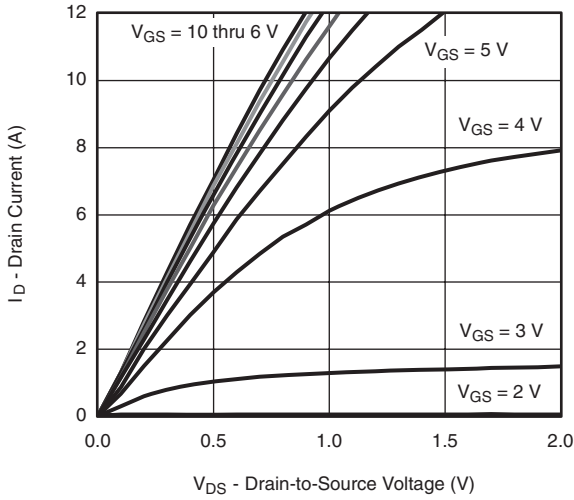
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

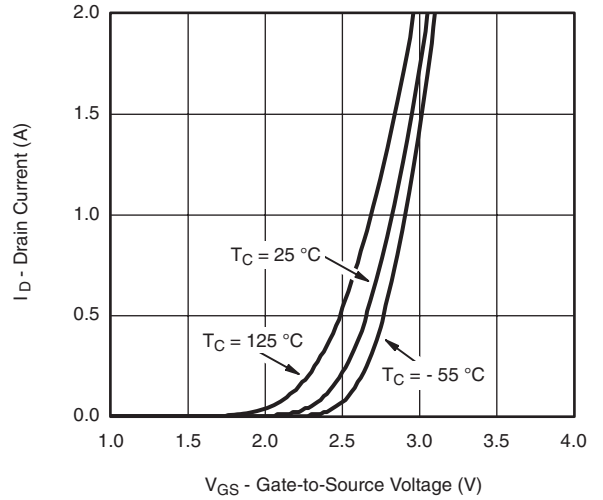
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



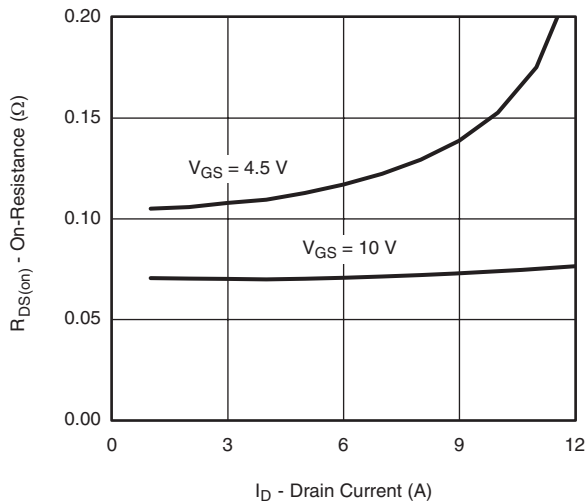
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



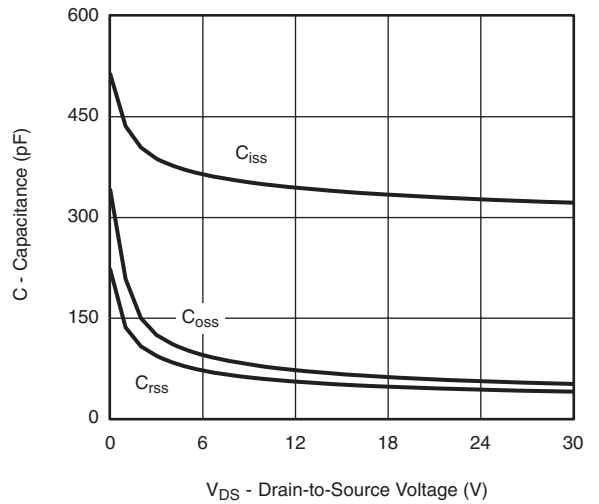
Output Characteristics



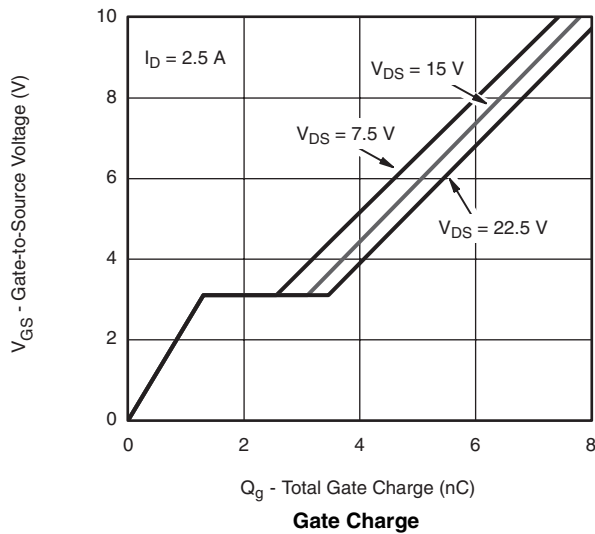
Transfer Characteristics



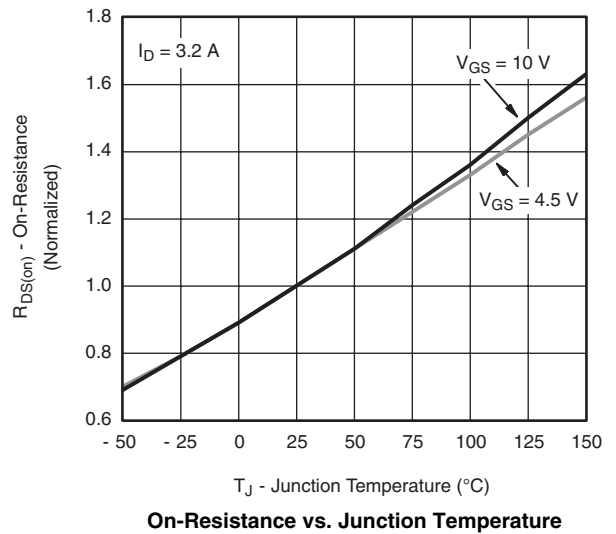
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



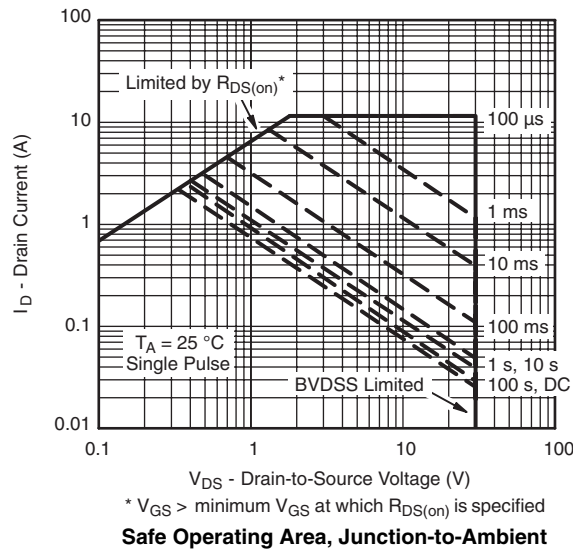
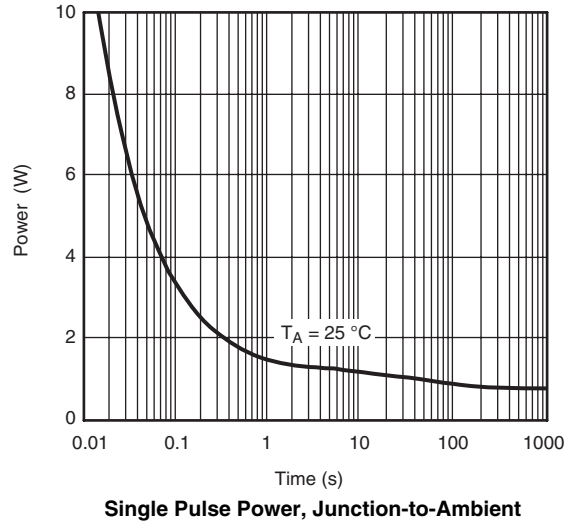
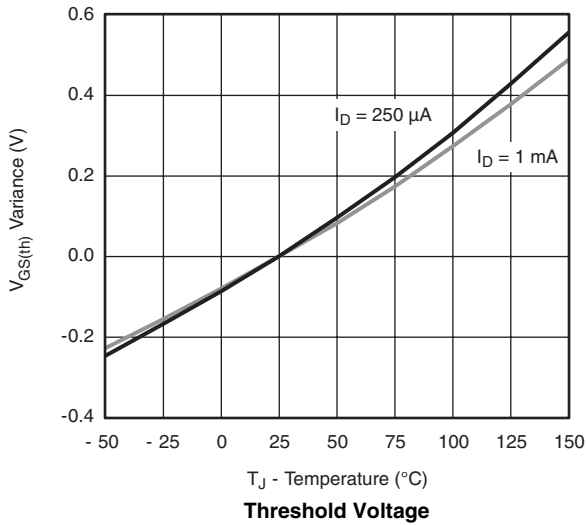
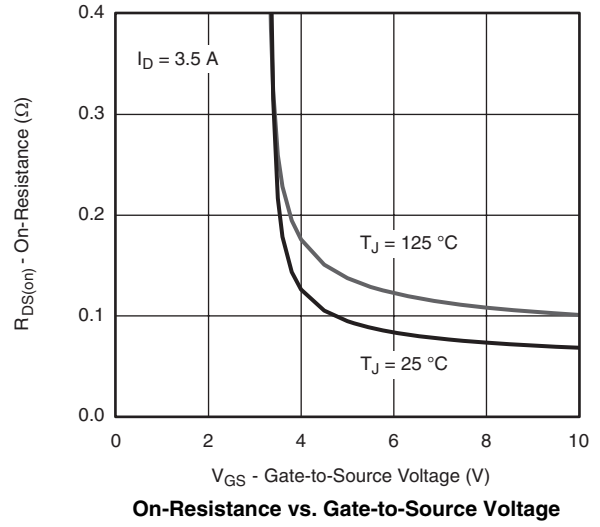
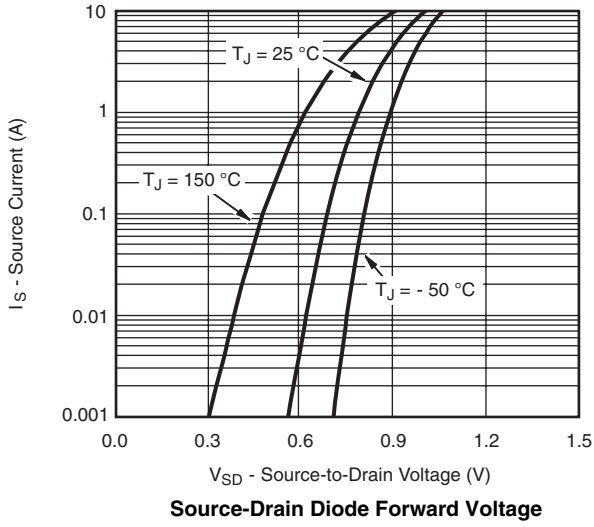
Gate Charge



On-Resistance vs. Junction Temperature

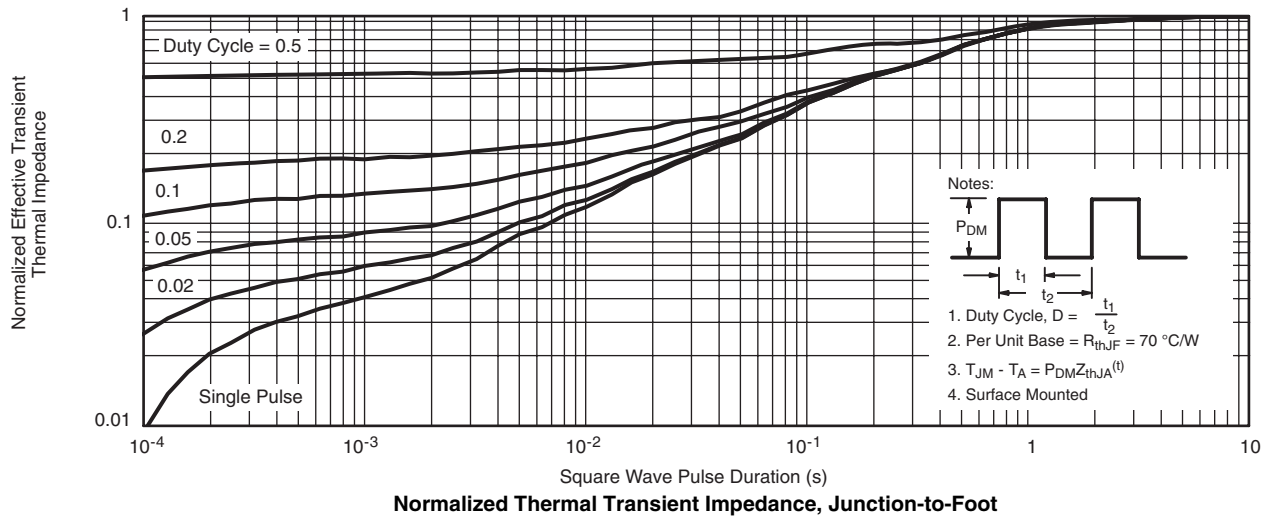
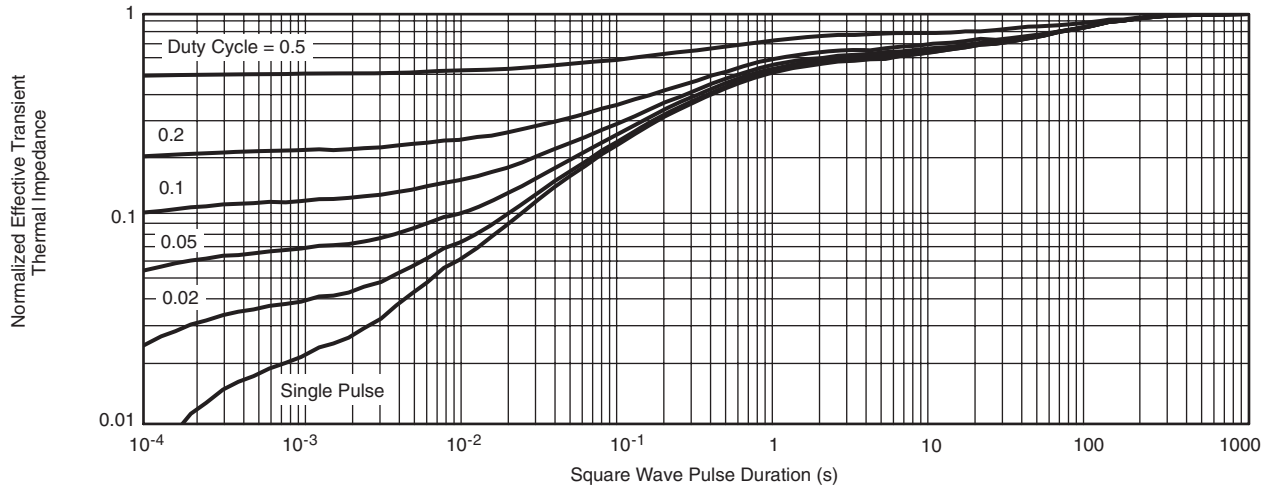


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